

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

2SC2551

HIGHT VOLTAGE CONTROL APPLICATIONS

PLASMA DISPLAY, NIXIE TUBE DRIVER APPLICATIONS

CATHODE RAY TUBE BRIGHTNESS CONTROL APPLICATIONS

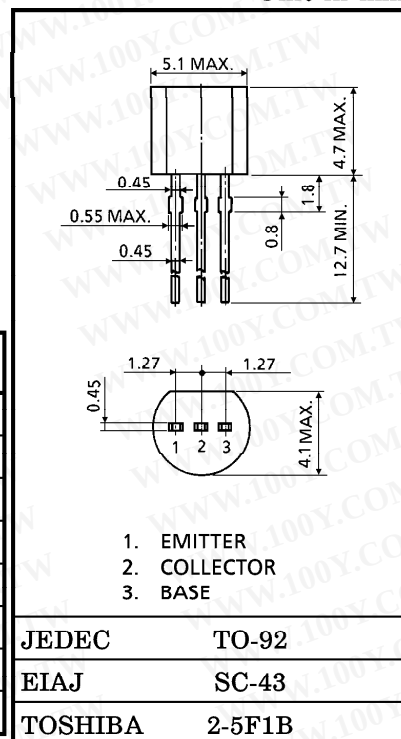
INDUSTRIAL APPLICATIONS

Unit in mm

- High Voltage : $V_{CBO}=300V$, $V_{CEO}=300V$
- Low Saturation Voltage : $V_{CE(sat)}=0.5V$ (Max.)
- Small Collector Output Capacitance : $C_{ob}=3pF$ (Typ.)
- Complementary to 2SA1091.

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	300	V
Collector-Emitter Voltage	V_{CEO}	300	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	100	mA
Base Current	I_B	20	mA
Collector Power Dissipation	P_C	400	mW
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55~150	$^\circ C$

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

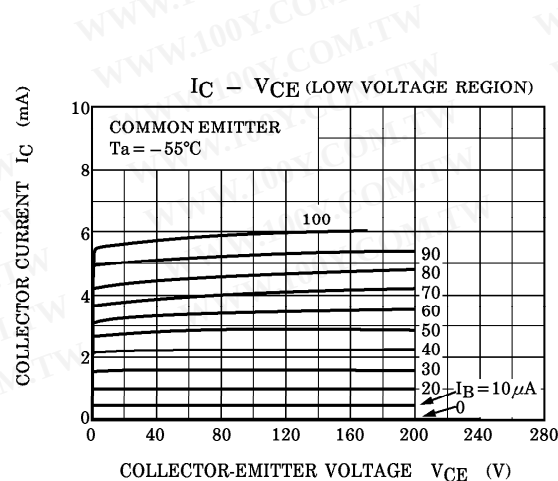
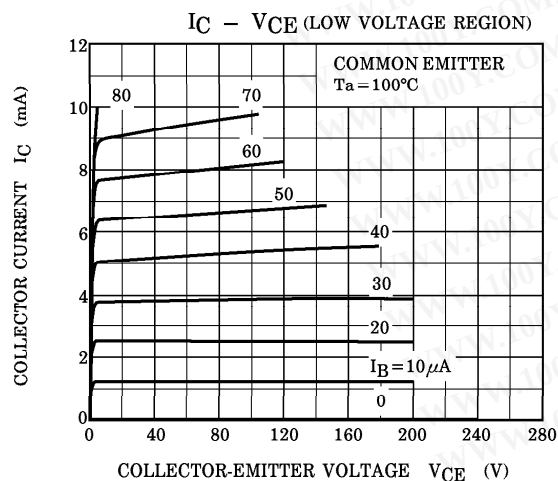
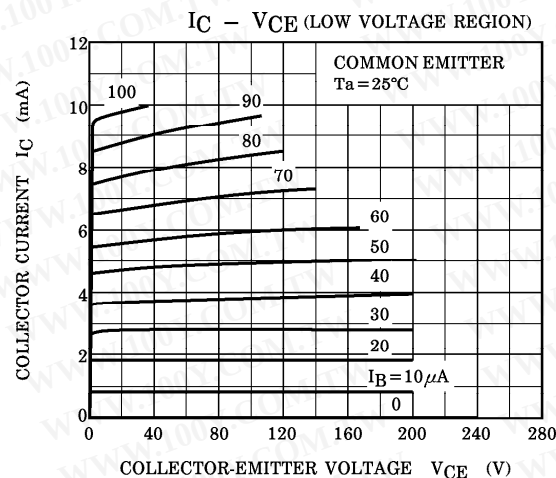
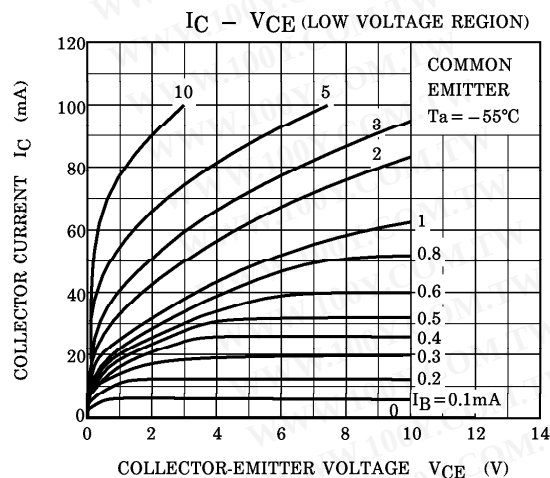
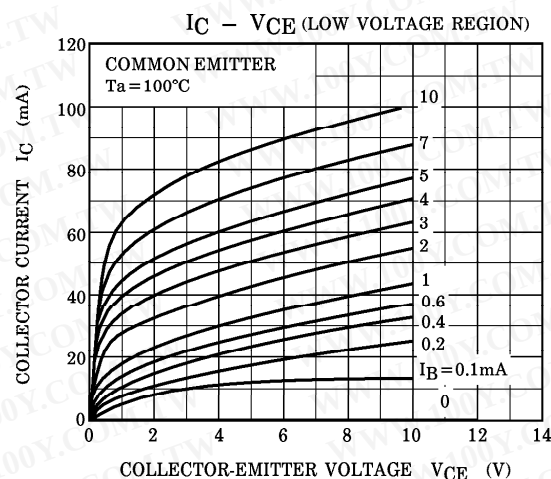
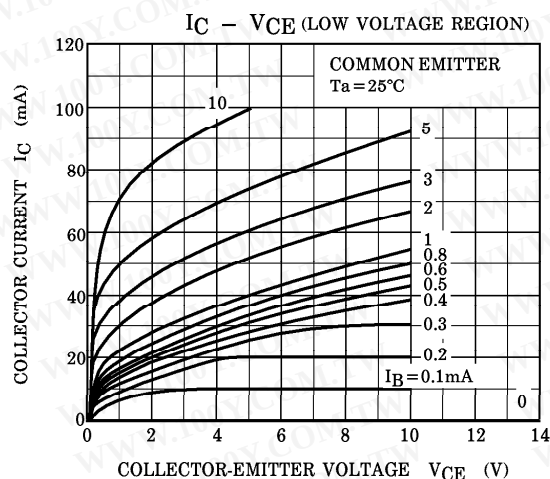
Weight : 0.21g

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=300V$, $I_E=0$	—	—	0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=6V$, $I_C=0$	—	—	0.1	μA
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=0.1mA$, $I_E=0$	300	—	—	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=1mA$, $I_B=0$	300	—	—	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE}=10V$, $I_C=20mA$	30	—	150	
	$h_{FE(2)}$	$V_{CE}=10V$, $I_C=1mA$	20	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=20mA$, $I_B=2mA$	—	—	0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=20mA$, $I_B=2mA$	50	—	1.2	V
Transition Frequency	f_T	$V_{CE}=10V$, $I_C=20mA$	—	80	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=20V$, $I_E=0$, $f=1MHz$	—	3	4	pF

Note : $h_{FE(1)}$ Classification R : 30~90, O : 50~150

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